nized as the leader of the UTA positron research program, and catalyzed its growth and strength through his vigor, vision and enthusiasm. The positron physics and chemistry programs present when he arrived evolved into the Center for Positron Studies in 1979 with McNutt as its director. The Center has been the site of positron lifetime studies in gases, liquid crystals, liquids and solids, of studies of positron-surface interactions, and of measurements of total, inelastic and differential cross-sections for the scattering of positrons by gases. The diversity of the activities of the Center is a testimony to the seemingly boundless energy and dedication of its former director.

McNutt keenly supported state, national and international research organizations. He was chairman of the Organizing Committee for the Sixth International Conference on Positron Annihilation, to be held in Arlington in 1982. It is particularly tragic that he died so shortly before an event that would have undoubtedly been a high point in his career and which would have granted him some of the recognition he so richly deserved.

MC NUTT

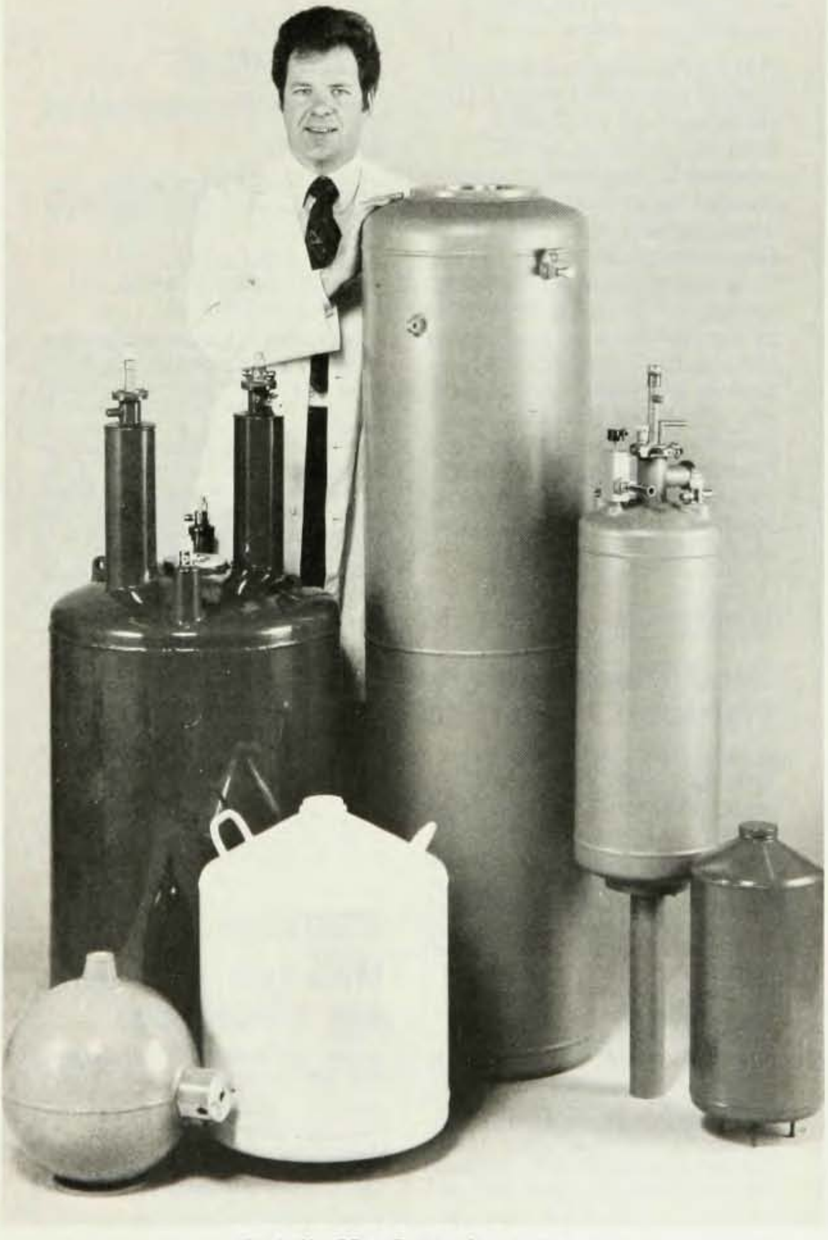
John's cheerful, friendly and energetic presence, and his scientific leadership, will be greatly missed by his colleagues and students.

PAUL G. COLEMAN
LEONARD M. DIANA
SURESH C. SHARMA
University of Texas at Arlington

James A. Jacobs

James Albert Jacobs, professor of physics emeritus at Virginia Polytechnic Institute and State University, died on 29 May 1980 in Blacksburg, Va.

Jacobs was born on 10 April 1913 in Sioux City and reared in Marshall-



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town, Iowa. He attended the University of Iowa where he won the coveted Sanxay Prize in his senior year. He earned all of his degrees at Iowa (BA in 1937, MS in 1940 and PhD in 1941, all in physics) and then, after serving as a research associate in physics there in 1941–42, he joined the Iowa faculty as assistant professor of physics in 1943. During the war years he served as director of a joint physics–engineering Office of Scientific Research and Development project of considerable size at Iowa on the development of the proximity fuze and he was then promoted directly to the rank of professor of physics in 1945. Jacobs continued at Iowa until 1960. In that year he joined the VPI & SU physics department as professor and head, and he continued to serve as head until 1973 while presiding over the majority of the department's growth. He retired from VPI & SU in 1978, but despite failing health he remained active there to the end through almost daily visits to the physics department for consultations with colleagues and students.

The death of Jim Jacobs is a sad reminder that even the best men are mortal. He was a experimental nuclear physicist as bright and capable as any of his contemporaries and a lecturer and teacher of outstanding power and lucidity. Though he was instrumental in the early development of nuclear physics equipment and research, he published relatively little himself, because his chief pleasure came, not from promoting his own career, but from helping younger people in his group to achieve positions of respect in physics. He was always ready to devote his time, his energy and his fine intellect to solving problems that puzzled his colleagues. Once solved, a problem lost interest for him, especially as regarded credit for the work. He was happy enough that he could then turn his talents to another task, never asking for personal recognition.

Jacobs was a congenial companion as well as an instructive leader. His cheerful manner and infectious laugh, combined with his ability in physics, made him an outstanding model well worth trying to emulate. He will not be forgotten by those who knew him well and those who did not have surely missed one of the wonderful men of our time.

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